

◆ Features:

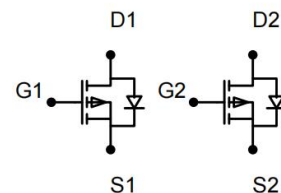
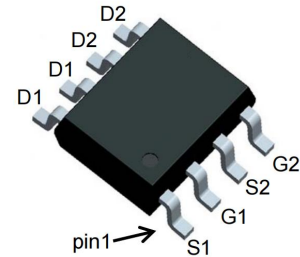
- ✧ Fast switching speed
开关速度快
- ✧ High input impedance and low level drive
高输入阻抗和低电平驱动
- ✧ Improved dv/dt capability, high ruggedness
提高 dv/dt 能力, 高耐用性

◆ Applications

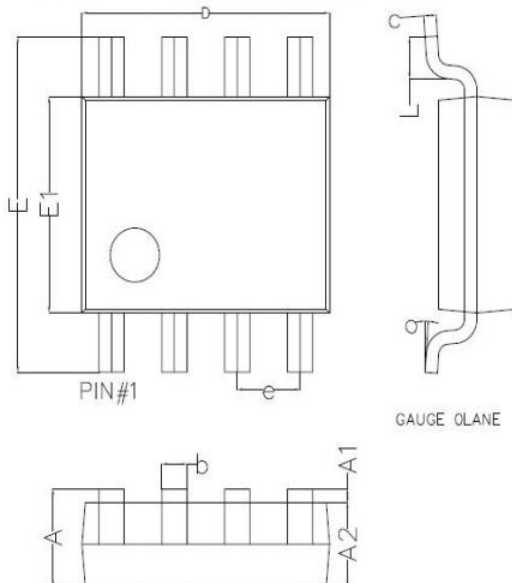
- ✧ Power management
能源管理
- ✧ Battery protection
电池保护
- ✧ Electronic lamp ballast
电子整流器



SOP-8



SOP8 Package Outline Dimensions



Symbol	Dim in mm		
	Min	Nor	Max
A	1.35	1.55	1.75
A1	0.02	0.065	0.10
A2	1.35	1.45	1.55
b	0.33	0.42	0.51
c	0.17	0.21	0.25
D	4.80	4.90	5.00
e	1.270 (BSC)		
E	5.80	6.00	6.20
E1	3.80	3.90	4.00
L	0.4	0.835	1.27
θ	0°	4°	8°

◆ Absolute Maximum Ratings (Tc=25°C)

Symbol	Parameters	Ratings	Unit
V _{DSS}	Drain-Source Voltage 漏源电压	-20	V
V _{GS}	Gate-Source Voltage-Continuous 栅源电压	±12	V
I _D	Drain Current-Continuous (Note 2) 漏极持续电流	-5	A
I _{DM}	Drain Current-Single Plused (Note 1) 漏极单次脉冲电流	-20	A
P _D	Power Dissipation (Note 2) 功率损耗	2.5	W
T _j	Max.Operating junction temperature 最大结温	150	°C

◆ Electrical characteristics (Tc=25°C unless otherwise noted)

Symbo l	Parameters	Min	Typ	Max	Units	Conditions
Static Characteristics						
B _{VDSS}	Drain-Source Breakdown VoltageCurrent (Note 1) 漏极击穿电压	-20	--	--	V	I _D =-250μA, V _{GS} =0V, T _J =25°C
V _{GS(th)}	Gate Threshold Voltage 栅极开启电压	0.40	0.72	-1.00	V	V _{DS} =V _{GS} , I _D =-250μA
R _{DS(on)}	Drain-Source On-Resistance 漏源导通电阻	--	57	65	mΩ	V _{GS} =-4.5V, I _D =-1A
I _{GSS}	Gate-Body Leakage Current 栅极漏电流	--	--	±100	nA	V _{GS} =±12V, V _{DS} =0
I _{DSS}	Zero Gate Voltage Drain Current 零栅极电压漏极电流	--	--	1	μA	V _{DS} =-20V, V _{GS} =0
g _{fs}	Forward Transconductance 正向跨导	--	6	--	S	V _{DS} =-5V, I _D =-1A

**OSS4953T****-20V P-CHANNEL MOSFET**

Switching Characteristics						
T _{d (on)}	Turn-On Delay Time 开启延迟时间	--	7	--	ns	V _{DS} =-10V, I _D =-5A, R _G =3Ω,V _{GS} =-4.5V (Note 2)
T _r	Rise Time 上升时间	--	15	--	ns	
T _{d (off)}	Turn-Off Delay Time 关闭延迟时间	--	30	--	ns	
T _f	Fall Time 下降时间	--	11	--	ns	
Q _g	Total Gate Charge 栅极总电荷	--	10	--	nC	V _{DS} =-16V V _{GS} =-4.5V I _D =-5A (Note 2)
Q _{gs}	Gate-Source Charge 栅源极电荷	--	1.7	--	nC	
Q _{gd}	Gate-Drain Charge 栅漏极电荷	--	3.5	--	nC	
Dynamic Characteristics						
C _{iss}	Input Capacitance 输入电容	--	600	--	pF	V _{DS} =-10V, V _{GS} =0, f=1MHz
C _{oss}	Output Capacitance 输出电容	--	125	-	pF	
C _{rss}	Reverse Transfer Capacitance 反向传输电容	--	100	--	pF	
I _S	Continuous Drain-Source Diode Forward Current (Note 2) 二极管导通正向持续电流	--	--	-5.0	A	
V _{SD}	Diode Forward On-Voltage 二极管正向导通电压	--	--	-1.2	V	I _S =-1A, V _{GS} =0
R _{th(j-c)}	Thermal Resistance, Junction to Case 结到外壳的热阻	--	--	50	°C/W	

Note 1: Repetitive Rating : Pulse width limited by maximum junction temperature

Note 2: Pulse test: PW ≤ 300us , duty cycle ≤ 2%.